

P-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY

V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)
- 60	0.0022 at V _{GS} = - 10 V	- 50	126 nC
	0.0026 at V _{GS} = - 4.5 V		

FEATURES

- DT-Trench Power MOSFET
- 100 % UIS Tested

APPLICATIONS

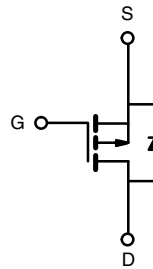
- Load Switch



RoHS
COMPLIANT



Top View



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DS}	- 60	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current ^d (T _J = 175 °C)	I _D	T _C = 25 °C	- 50
		T _C = 100 °C	- 37
Pulsed Drain Current	I _{DM}	-200	A
Avalanche Current	I _{AS}	-46	
Single Pulse Avalanche Energy ^a	E _{AS}	753	mJ
Power Dissipation	P _D	T _C = 25 °C ^c	161
		T _A = 25 °C ^b	3.37
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYPICAL	UNIT
Junction-to-Ambient	R _{thJA}	40	°C/W
Junction-to-Case	R _{thJC}	0.75	

Notes

- Duty cycle ≤ 1 %.
- When mounted on 1" square PCB (FR4 material).
- See SOA curve for voltage derating.

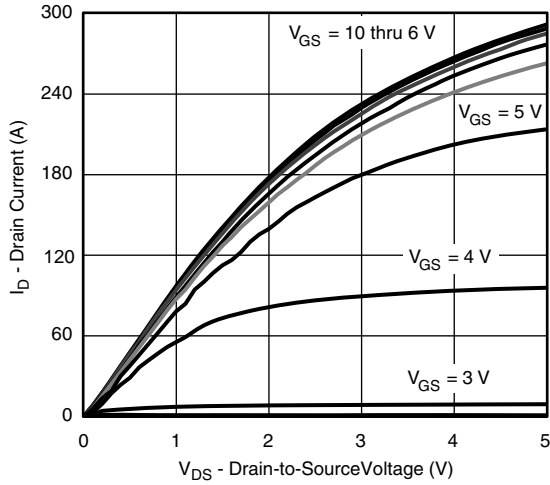
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-60			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T$	$I_D = -250\text{ }\mu\text{A}$		58		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			-5.2		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-1		-3	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -60\text{ V}, V_{GS} = 0\text{ V}$			-10	μA
		$V_{DS} = -60\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			-25	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5\text{ V}, V_{GS} = -10\text{ V}$	-50			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -30\text{ A}$		0.022	0.027	Ω
		$V_{GS} = -4.5\text{ V}, I_D = -20\text{ A}$		0.026	0.033	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15\text{ V}, I_D = -30\text{ A}$	16			S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = -25\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		3376		pF
Output Capacitance	C_{oss}			1090		
Reverse Transfer Capacitance	C_{rss}			595		
Total Gate Charge	Q_g	$V_{DS} = -30\text{ V}, V_{GS} = -10\text{ V}, I_D = -30\text{ A}$		126	195	nC
Gate-Source Charge	Q_{gs}			36		
Gate-Drain Charge	Q_{gd}			73		
Gate Resistance	R_g	$f = 1\text{ MHz}$		5.5		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -2\text{ V}, R_L = 2\text{ }\Omega$ $I_D \cong -10\text{ A}, V_{GEN} = -10\text{ V}, R_g = 1\text{ }\Omega$		35		ns
Rise Time	t_r			96		
Turn-Off Delay Time	$t_{d(off)}$			50		
Fall Time	t_f			82		
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			-50	A
Pulse Diode Forward Current ^a	I_{SM}				-200	
Body Diode Voltage	V_{SD}	$I_S = -30\text{ A}$		-1	-1.5	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -30\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		75	108	ns
Body Diode Reverse Recovery Charge	Q_{rr}			149	320	nC
Reverse Recovery Fall Time	t_a			29		ns
Reverse Recovery Rise Time	t_b			16		

Notes:

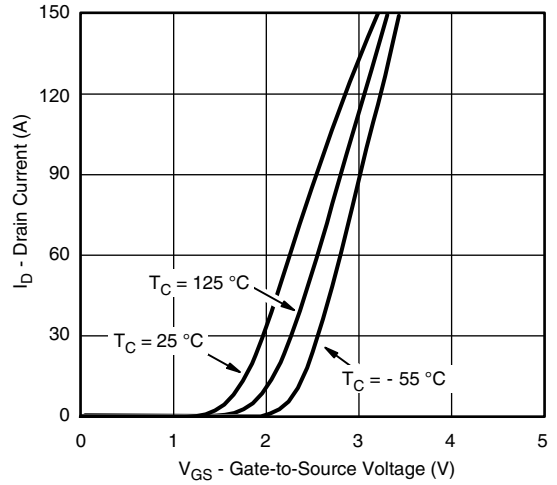
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

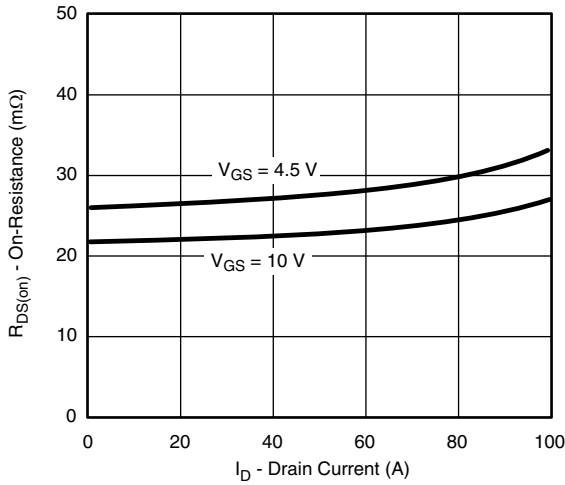
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



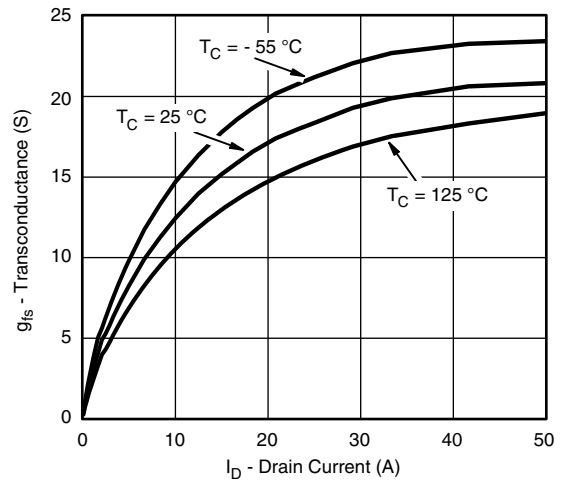
Output Characteristics



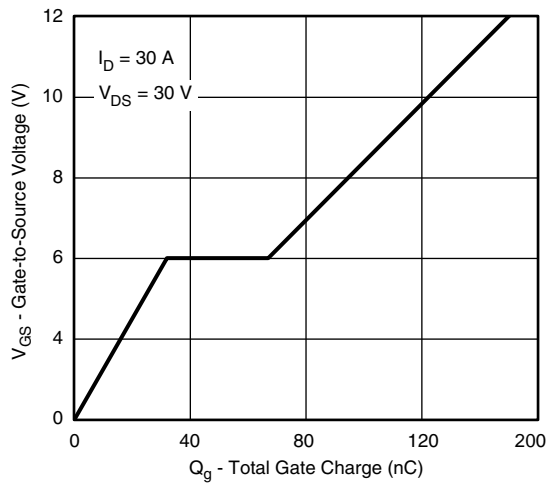
Transfer Characteristics



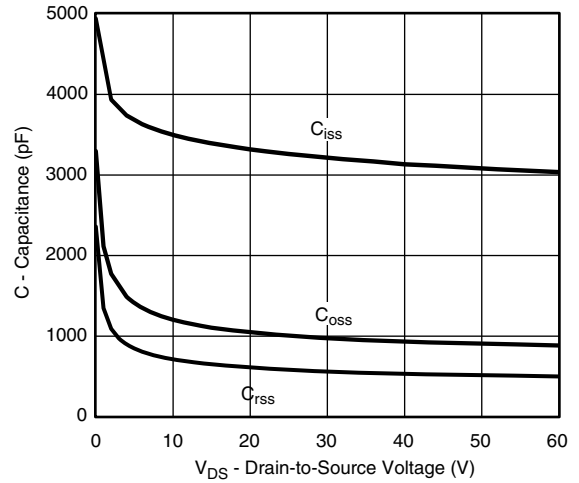
On-Resistance vs. Drain Current



Transconductance

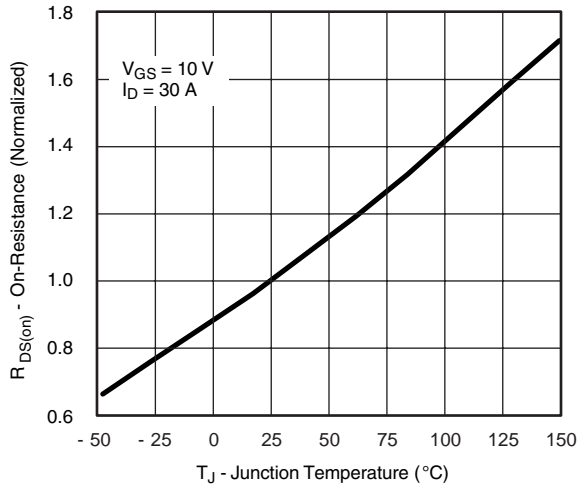


Gate Charge

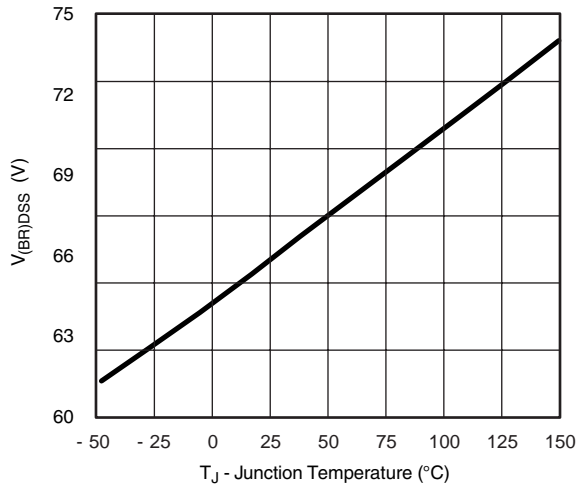


Capacitance

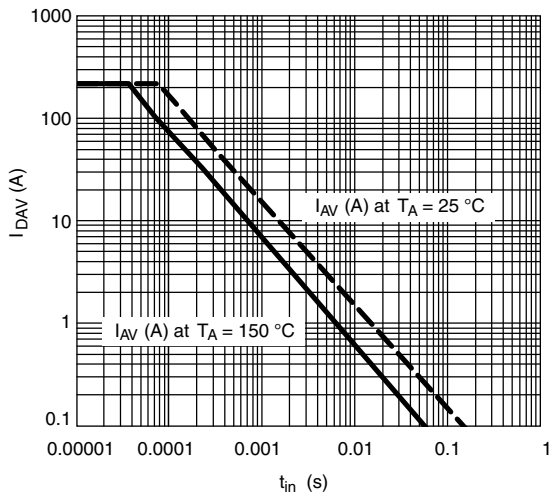
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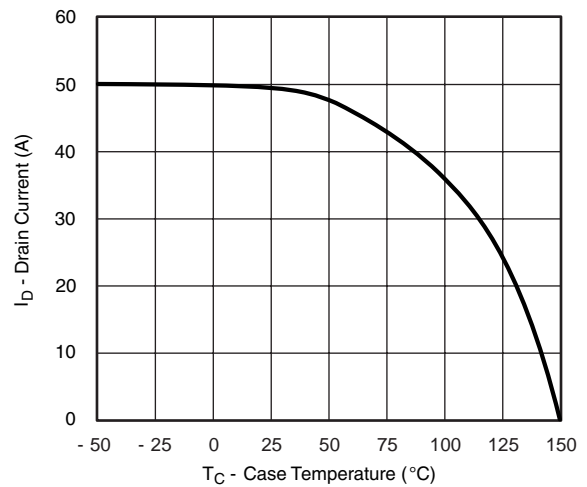
On-Resistance vs. Junction Temperature



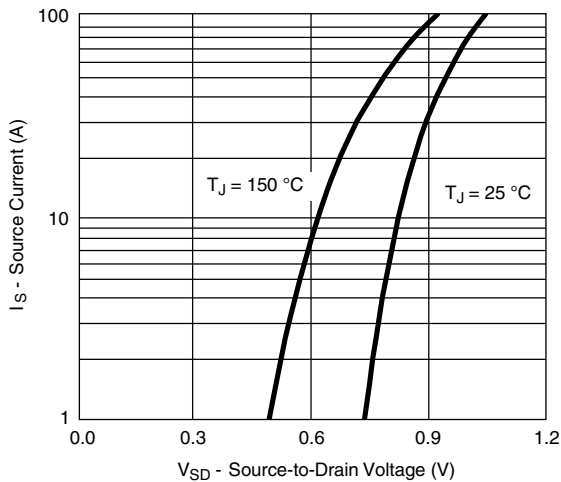
Drain Source Breakdown vs. Junction Temperature



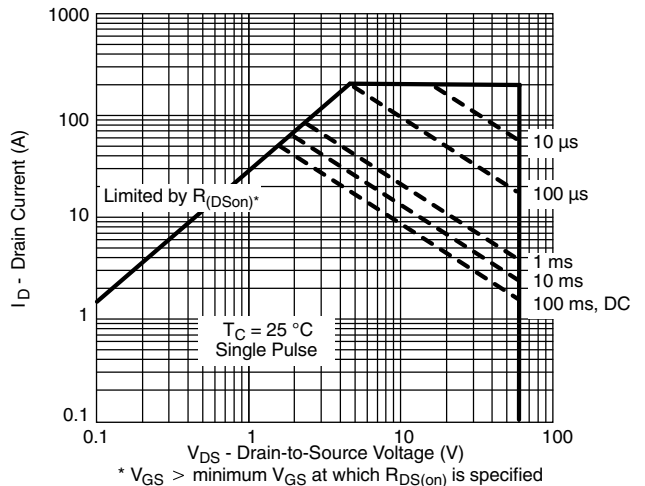
Avalanche Current vs. Time



Maximum Avalanche and Drain Current vs. Case Temperature

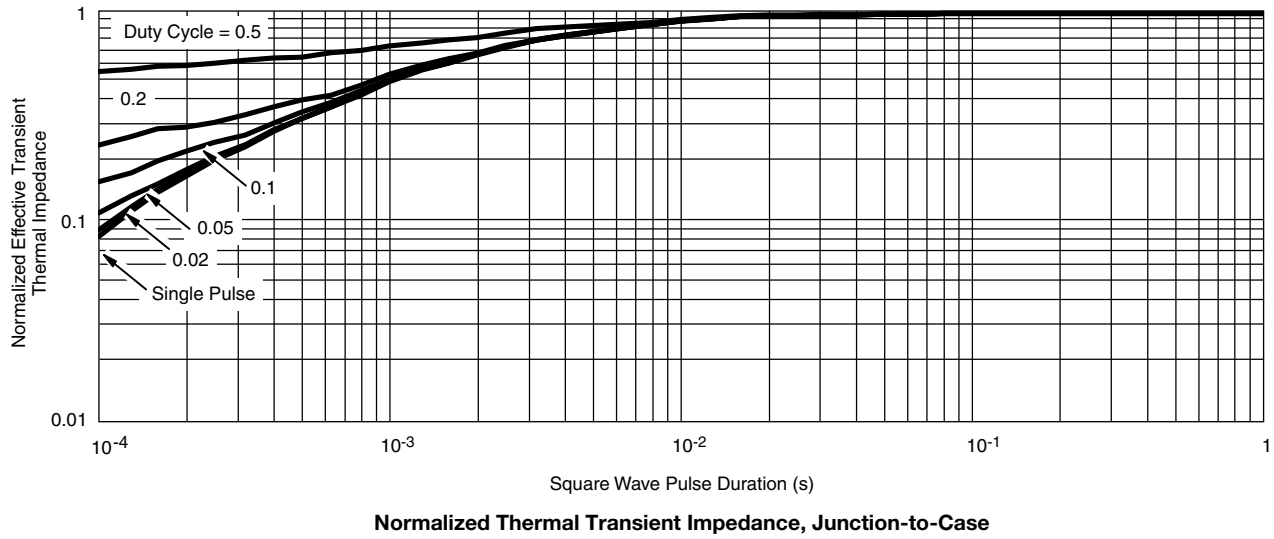


Source-Drain Diode Forward Voltage

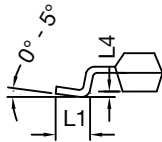
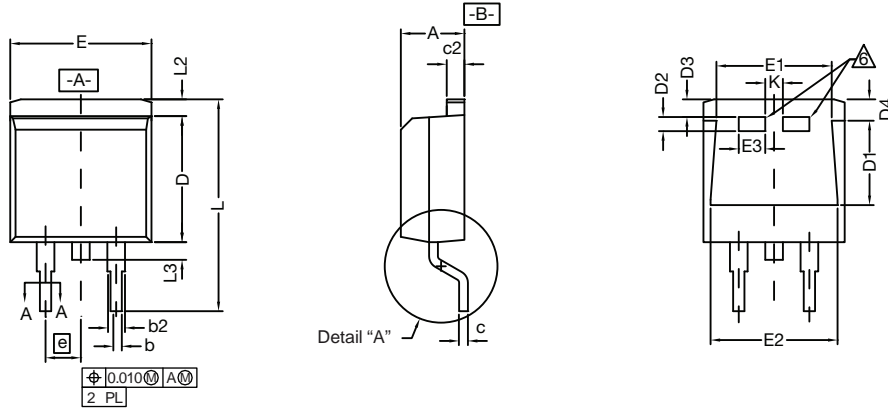


Safe Operating Area

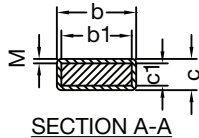
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



TO-263 (D²PAK): 3-LEAD

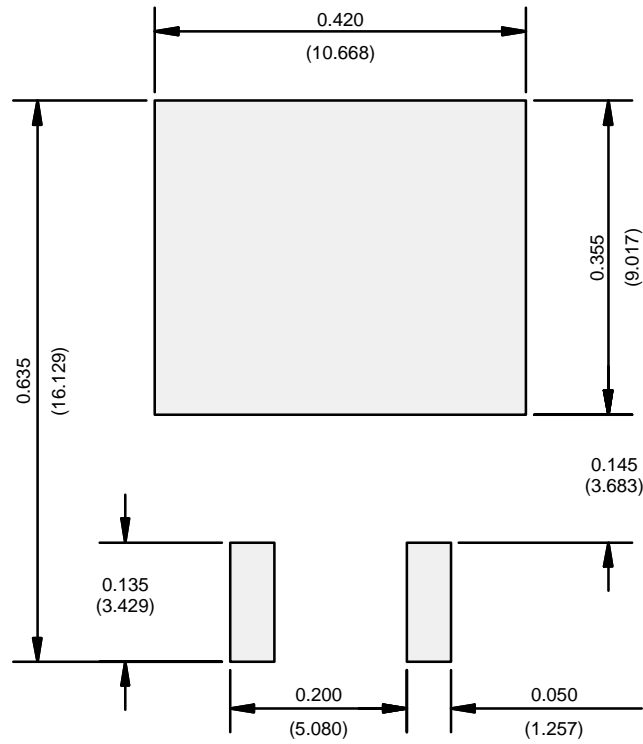


DETAIL A (ROTATED 90°)



DIM.	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	0.160	0.190	4.064	4.826	
b	0.020	0.039	0.508	0.990	
b1	0.020	0.035	0.508	0.889	
b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457
	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
	Thick lead	0.023	0.027	0.584	0.685
c2	0.045	0.055	1.143	1.397	
D	0.340	0.380	8.636	9.652	
D1	0.220	0.240	5.588	6.096	
D2	0.038	0.042	0.965	1.067	
D3	0.045	0.055	1.143	1.397	
D4	0.044	0.052	1.118	1.321	
E	0.380	0.410	9.652	10.414	
E1	0.245	-	6.223	-	
E2	0.355	0.375	9.017	9.525	
E3	0.072	0.078	1.829	1.981	
e	0.100 BSC		2.54 BSC		
K	0.045	0.055	1.143	1.397	
L	0.575	0.625	14.605	15.875	
L1	0.090	0.110	2.286	2.794	
L2	0.040	0.055	1.016	1.397	
L3	0.050	0.070	1.270	1.778	
L4	0.010 BSC		0.254 BSC		
M	-	0.002	-	0.050	

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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